

February 1989 Revised August 1999

74F899

9-Bit Latchable Transceiver with Parity Generator/Checker

General Description

The 74F899 is a 9-bit to 9-bit parity transceiver with transparent latches. The device can operate as a feed-through transceiver or it can generate/check parity from the 8-bit data busses in either direction. It has a guaranteed current sinking capability of 24 mA at the A-bus and 64 mA at the B-bus.

The 74F899 features independent latch enables for the A-to-B direction and the B-to-A direction, a select pin for ODD/EVEN parity, and separate error signal output pins for checking parity.

Features

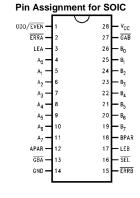
- Latchable transceiver with output sink of 24 mA at the A-bus and 64 mA at the B-bus
- Option to select generate parity and check or "feed-through" data/parity in directions A-to-B or B-to-A
- Independent latch enables for A-to-B and B-to-A directions
- Select pin for ODD/EVEN parity
- ERRA and ERRB output pins for parity checking
- Ability to simultaneously generate and check parity
- May be used in systems applications in place of the 74F543 and 74F280
- May be used in system applications in place of the 74F657 and 74F373 (no need to change T/R to check parity)

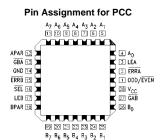
Ordering Code:

Order Number	Package Number	Package Description
74F899SC	M28B	28-Lead Small Outline Integrated Circuit (SOIC), JEDEC MS-013, 0.300 Wide
74F899QC	V28A	28-Lead Plastic Lead Chip Carrier (PLCC), JEDEC MO-047, 0,450 Square

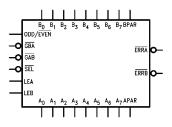
Devices also available in Tape and Reel. Specify by appending the suffix letter "X" to the ordering code.

Connection Diagrams





Logic Symbol



© 1999 Fairchild Semiconductor Corporation

DS010195

Input Loading/Fan-Out

		HIGH/LOW			
Pin Names	Description	U.L.	Input I _{IH} /I _{IL}		
		HIGH/LOW	Output I _{OH} /I _{OL}		
A ₀ -A ₇	Data Inputs/	1.0/1.0	20 μA/–0.6 mA		
	Data Outputs	150/40	−3 mA/24 mA		
B ₀ –B ₇	Data Inputs/	1.0/1.0	20 μA/–0.6 mA		
	Data Outputs	600/106.6	–12 mA/64 mA		
APAR	A Bus Parity	1.0/1.0	20 μA/–0.6 mA		
	Input/Output	150/40	−3 mA/24 mA		
BPAR	B Bus Parity	1.0/1.0	20 μA/–0.6 mA		
	Input/Output	600/106.6	–12 mA/64 mA		
ODD/EVEN	Parity Select Input	1.0/1.0	20 μA/–0.6 mA		
GBA, GAB	Output Enable Inputs	1.0/1.0	20 μA/–0.6 mA		
SEL	Mode Select Input	1.0/1.0	20 μA/–0.6 mA		
LEA, LEB	Latch Enable Inputs	1.0/1.0	20 μA/–0.6 mA		
ERRA, ERRB	Error Signal Outputs	50/33.3	−1 mA/20 mA		

Pin Descriptions

Pin Names	Description						
A ₀ -A ₇	A Bus Data Inputs/Data Outputs						
B ₀ -B ₇	B Bus Data Inputs/Data Outputs						
APAR, BPAR	A and B Bus Parity Inputs						
ODD/EVEN	ODD/EVEN Parity Select, Active LOW for EVEN Parity						
GBA, GAB	Output Enables for A or B Bus, Active LOW						
SEL	Select Pin for Feed-Through or Generate Mode, LOW for Generate Mode						
LEA, LEB	Latch Enables for A and B Latches, HIGH for Transparent Mode						
ERRA, ERRB	Error Signals for Checking Generated Parity with Parity In, LOW if Error Occurs						

Functional Description

The 74F899 has three principal modes of operation which are outlined below. These modes apply to both the A-to-B and B-to-A directions.

- Bus A (B) communicates to Bus B (A), parity is generated and passed on to the B (A) Bus as BPAR (APAR). If LEB (LEA) is HIGH and the Mode Select (SEL) is LOW, the parity generated from B[0:7] (A[0:7]) can be checked and monitored by ERRB (ERRA).
- Bus A (B) communicates to Bus B (A) in a feed-through mode if <u>SEL</u> is <u>HIGH</u>. <u>Parity</u> is still generated and checked as <u>ERRA</u> and <u>ERRB</u> in the feed-through mode (can be used as an interrupt to signal a data/parity bit error to the CPU).
- Independent Latch Enables (LEA and LEB) allow other permutations of generating/checking (see Function Table).

Function Table

Inputs							
GAB	GBA	GBA SEL LEA LEE			Operation		
Н	Н	Х	Х	Х	Busses A and B are 3-STATE.		
Н	L	L	L	Н	Generates parity from B[0:7] based on O/E (Note 1). Generated parity → APAR. Generated parity checked against BPAR and output as ERRB.		
Н	L	L	Н	Н	Generates parity from B[0:7] based on O/\overline{E} . Generated parity \to APAR. Generated parity checked against BPAR and output as \overline{ERRB} . Generated parity also fed back through the A latch for generate/check as \overline{ERRA} .		
Н	L	L	Х	L	Generates parity from B latch data based on O/E. Generated parity → APAR. Generated parity checked against latched BPAR and output as ERRB.		
Н	L	Н	Х	Н	BPAR/B[0:7] \rightarrow APAR/A0:7] Feed-through mode. Generated parity checked against BPAR and output as ERRB.		
Н	L	Н	Н	Н	$BPAR/B[0:7] \to APAR/A[0:7]$		
					Feed-through mode. Generated parity checked against BPAR and output <u>as ERRB.</u> Generated parity also fed back through the A latch for generate/check as ERRA.		
L	Н	L	Н	L	Generates parity for A[0:7] based on O/ \overline{E} . Generated parity \to BPAR. Generated parity checked against APAR and output as ERRA.		
L	Н	L	Н	Н	Generates parity from A[0:7] based on O/\overline{E} . Generated parity \rightarrow BPAR. Generated parity checked against APAR and output as \overline{ERRA} . Generated parity also fed back through the B latch for generate/check as \overline{ERRB} .		
L	Н	L	L	Х	Generates parity from A latch data based on O/E. Generated parity → BPAR. Generated parity checked against latched APAR and output as ERRA.		
L	Н	Н	Н	L	$APAR/A[0:7] \to BPAR/B[0:7]$		
					Feed-through mode. Generated parity checked against APAR and output as ERRA.		
L	Н	Н	Н	Н	$APAR/A[0:7] \to BPAR/B[0:7]$		
					Feed-through mode. Generated parity checked against APAR and output <u>as ERRA.</u> Generated parity also fed back through the B latch for generate/check as ERRB.		

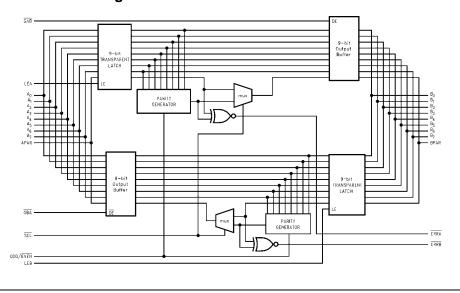
H = HIGH Voltage Level

Note 1: O/E = ODD/EVEN

L = LOW Voltage Level

X = Immaterial

Functional Block Diagram



Absolute Maximum Ratings(Note 2)

Recommended Operating Conditions

Storage Temperature -65°C to +150°C

 $\begin{array}{lll} \mbox{Ambient Temperature under Bias} & -55^{\circ}\mbox{C to } +125^{\circ}\mbox{C} \\ \mbox{Junction Temperature under Bias} & -55^{\circ}\mbox{C to } +150^{\circ}\mbox{C} \\ \mbox{V}_{\mbox{CC}} \mbox{ Pin Potential to Ground Pin} & -0.5\mbox{V to } +7.0\mbox{V} \\ \end{array}$

Voltage Applied to Output $in \ HIGH \ State \ (with \ V_{CC} = 0V)$

 $\begin{array}{ll} \mbox{Standard Output} & -0.5\mbox{V to V}_{\mbox{CC}} \\ \mbox{3-STATE Output} & -0.5\mbox{V to } +5.5\mbox{V} \end{array}$

Current Applied to Output

in LOW State (Max) Twice the Rated I_{OL} (mA) ESD Last Passing Voltage (Min) 4000V

Free Air Ambient Temperature 0°C to +70°C Supply Voltage +4.5V to +5.5V

Note 2: Absolute maximum ratings are values beyond which the device may be damaged or have its useful life impaired. Functional operation under these conditions is not implied.

Note 3: Either voltage limit or current limit is sufficient to protect inputs.

DC Electrical Characteristics

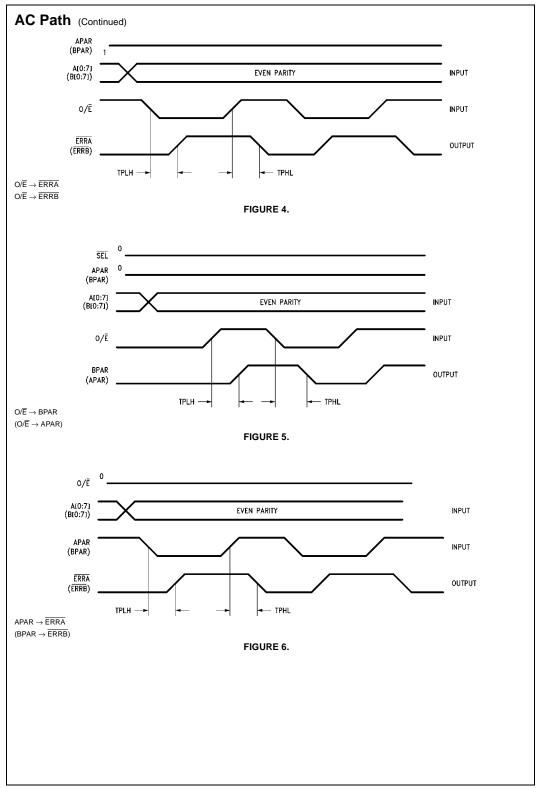
Symbol	l Parameter		Min	Тур	Max	Units	v _{cc}	Conditions
V _{IH}	Input HIGH Voltage		2.0			V		Recognized as a
								HIGH Signal
V _{IL}	Input LOW Voltage				8.0	V		Recognized as a
								LOW Signal
V _{CD}	Input Clamp Diode Voltage)			-1.2	V	Min	I _{IN} = -18 mA
V _{OH}	Output HIGH 10	0% V _{CC}	2.5					$I_{OH} = -1 \text{ mA}$
	Voltage 10	0% V _{CC}	2.4					$I_{OH} = -3 \text{ mA}$
	10	0% V _{CC}	2.0			V		$I_{OH} = -15 \text{ mA } (B_n, BPAR)$
	5	5% V _{CC}	2.7					$I_{OH} = -1 \text{ mA}$
		5% V _{CC}	2.7					$I_{OH} = -3 \text{ mA}$
V _{OL}	Output LOW 10	0% V _{CC}			0.5			I _{OL} = 20 mA
	Voltage							(A _n , APAR, ERRA, ERRB)
	5	5% V _{CC}			0.55	V		I _{OL} = 24 mA
								(A _n , APAR, ERRA, ERRB)
	10	0% V _{CC}			0.55			$I_{OL} = 64 \text{ mA } (B_n, BPAR)$
V _{TH}	Input Threshold Voltage			1.45		V		±0.1V, Sweep Edge Rate must be > 1V/50 ns
V _{OLV}	Negative Ground Bounce			1.0		V		Observed on "quiet" output during
	Voltage			1.0		v		simultaneous switching of remaining outputs
V _{OLP}	Positive Ground Bounce			4.0		V		Observed on "quiet" output during
	Voltage			1.0		v		simultaneous switching of remaining outputs
I _{IL}	Input Low Current				-0.6	mA	Max	V _{IN} = 0.5V
I _{IH}	Input HIGH				5.0	μА	Max	V _{IN} = 2.7V
	Current				3.0	μΛ	IVIAX	VIN - 2.7 V
I _{BVI}	Input HIGH Current				7.0	μА	Max	V _{IN} = 7.0V
	Breakdown Test				7.0	μΛ	IVIAX	(ODD/EVEN, GBA, GAB, SEL, LEA, LEB)
I _{BVIT}	Input HIGH Current				0.5	mA	Max	V _{IN} = 5.5V
	Breakdown (I/O)				0.5	IIIA	IVIAX	$(A_n, B_n, A_{PAR}, B_{PAR})$
I _{CEX}	Output HIGH				50	μА	Max	V _{OLIT} = V _{CC}
	Leakage Current				30	μΑ	IVIGA	VOUI - VCC
V _{ID}	Input Leakage		4.75			V	0.0	$I_{ID} = 1.9 \mu\text{A}$
	Test		4.73			· ·	0.0	All Other Pins Grounded
I _{OD}	Output Leakage				3.75	μА	0.0	V _{IOD} = 150 mV
	Circuit Current				3.73	μΑ	0.0	All Other Pins Grounded
I _{IL}	Input Low Current				-0.6	mA	Max	V _{IN} = 0.5V
I _{IH+}	Output Leakage Current				70	μА	Max	V _{I/O} = 2.7V
I _{OZH}	Current					μΑ	IVIGA	(A _n , B _n , APAR, BPAR)
				-			-	

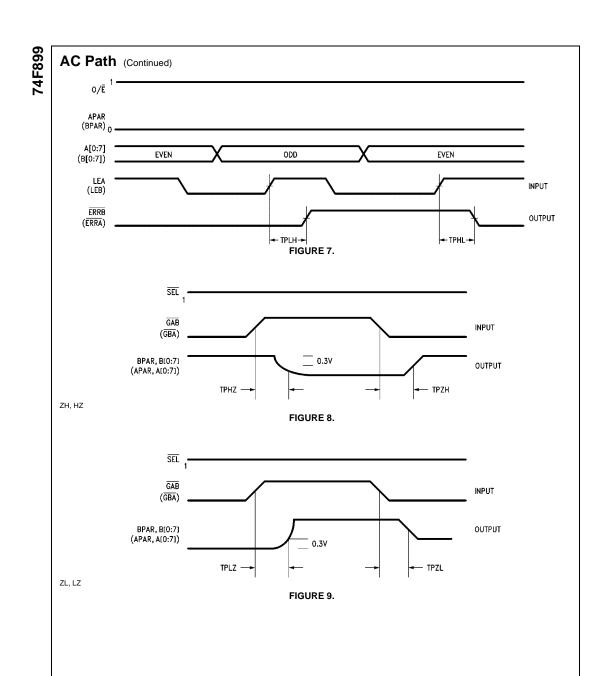
DC Electrical Characteristics (Continued)

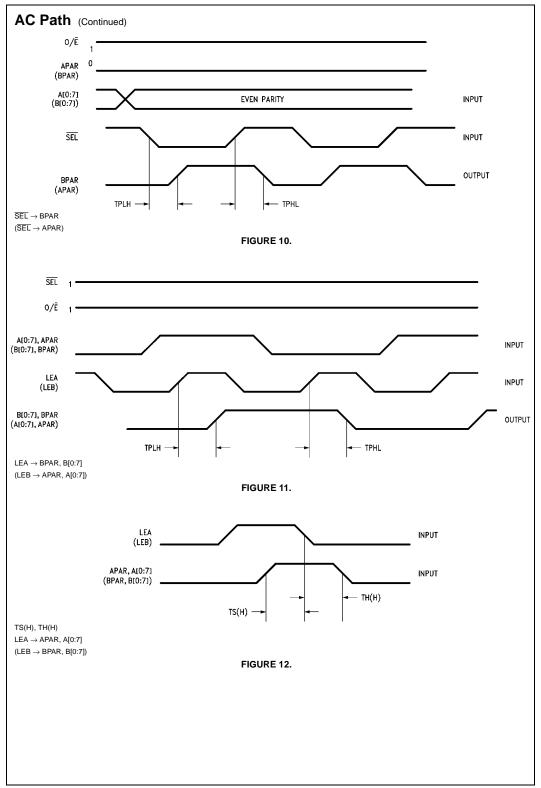
Symbol	Parameter	Min	Тур	Max	Units	v _{cc}	Conditions
I _{IL+}	Output Leakage			-650	μА	Max	$V_{I/O} = 0.5V$
I _{OZL}	Current			-630	μА	IVIAX	(A _n , B _n , APAR, BPAR)
Ios	Output Short-Circuit Current	-60		-150		Max	V _{OUT} = 0V
					mA		$(A_n, APAR, \overline{ERRA}, \overline{ERRB})$
		-100		-225		Max	$V_{OUT} = 0V (B_n, BPAR)$
I _{ZZ}	Bus Drainage Test			500	μΑ	0.0V	V _{OUT} = 5.25V
I _{CCH}	Power Supply Current		132	155	mA	Max	V _O = HIGH
I _{CCL}	Power Supply Current		178	210	mA	Max	$V_O = LOW, GAB = LOW,$
							GBA = HIGH, V _{IL} = LOW
I _{CCZ}	Power Supply Current		160	190	mA	Max	V _O = HIGH Z

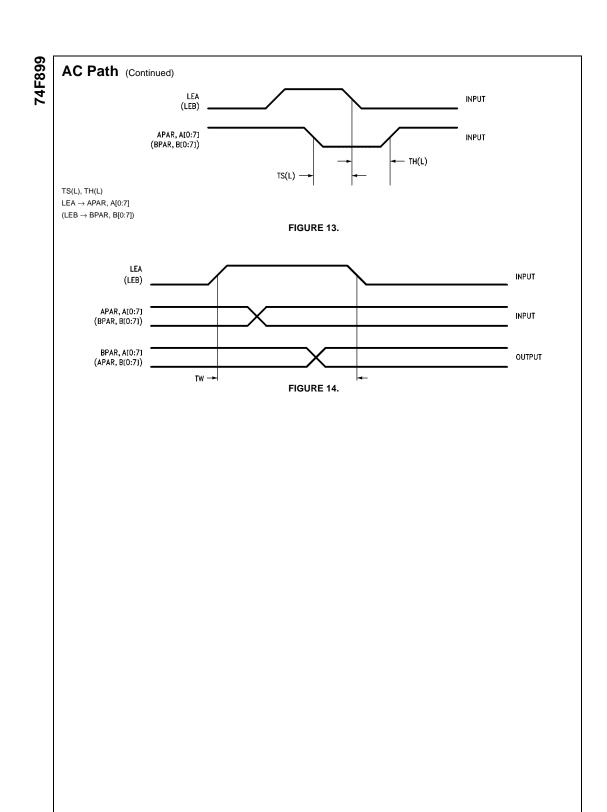
AC Electrical Characteristics

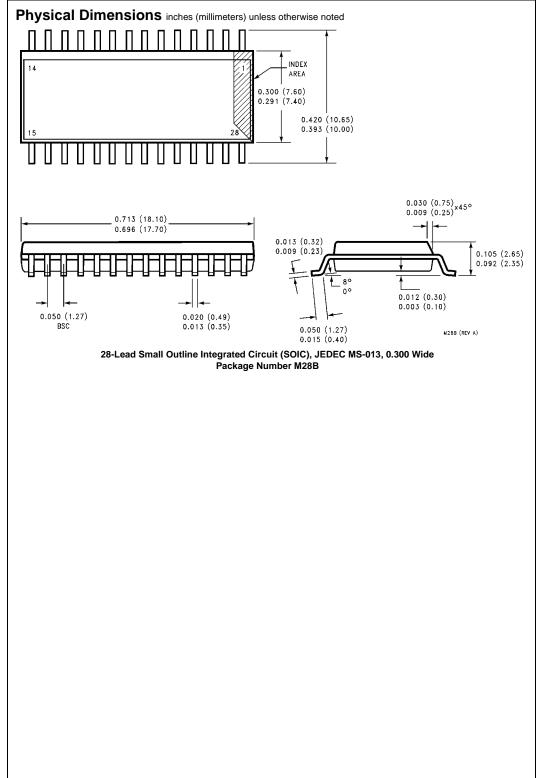
			T _A = +25°C		T _A = 0°C	to +70°C		
Symbol	B		V _{CC} = +5.0\	<i>(</i>	v _{cc} =	+5.0V	11-11-	Figure
	Parameter		C _L = 50 pF		C _L = 50 pF		Units	Number
		Min	Тур	Max	Min	Max	•	
t _{PLH}	Propagation Delay	4.0	7.5	13.0	4.0	14.0	200	Figure 1
t _{PHL}	A _n , APAR to B _n , BPAR	4.0	8.5	13.0	4.0	14.0	ns	Figure 1
t _{PLH}	Propagation Delay	7.5	12.0	17.0	7.5	18.0	ns	Figure 2
t _{PHL}	A _n , B _n to BPAR, APAR	7.5	12.5	17.0	7.5	18.0	115	Figure 2
t _{PLH}	Propagation Delay	7.5	12.0	17.0	7.5	18.0	no	Figure 3
t_{PHL}	A _n , B _n to ERRA, ERRB	7.5	12.5	17.0	7.5	18.0	ns	Figure 3
t _{PLH}	Propagation Delay	4.5	7.5	11.0	4.5	12.0		Fi
t _{PHL}	ODD/EVEN to ERRA, ERRB	4.5	8.0	11.0	4.5	12.0	ns	Figure 4
t _{PLH}	Propagation Delay	4.5	7.5	11.5	4.5	12.5		
t _{PHL}	ODD/EVEN to APAR, BPAR	4.5	8.5	11.5	4.5	12.5	ns	Figure 5
t _{PLH}	Propagation Delay	5.5	9.0	13.0	5.5	14.0		
t _{PHL}	APAR, BPAR to ERRA, ERRB	5.5	9.5	13.0	5.5	14.0	ns	Figure 6
t _{PLH}	LEA/LEB to	9.5	13.0	17.5	7.5	18.0		
t _{PHL}	ERRA /ERRB	9.7		17.5	7.5	18.0	ns	Figure 7
t _{PLH}	Propagation Delay	3.0	6.0	10.0	3.0	11.0		
t _{PHL}	SEL to APAR, BPAR	3.0	7.0	10.0	3.0	11.0	ns	Figure 10
t _{PLH}	Propagation Delay	3.5	7.0	10.0	3.5	11.0		- 44
t _{PHL}	LEB to A _n , APAR	3.5	8.0	10.0	3.5	11.0	ns	Figure 11
t _{PLH}	Propagation Delay	3.5	6.5	10.0	3.5	11.0		Figure 44
t _{PHL}	LEA to B _n , BPAR	3.5	7.5	10.0	3.5	11.0	ns	Figure 11
t _{PZH}	Output Enable Time	1.0	4.5	10.0	1.0	11.0		İ
t _{PZL}	GBA or GAB to A _n ,	1.0	6.5	10.0	1.0	11.0	ns	Figure 8, Figure 9
	APAR or B _n , BPAR							. iguio c
t _{PHZ}	Output Disable Time	1.0	4.0	7.0	1.0	8.0		
t _{PLZ}	GBA or GAB to An,	1.0	4.0	7.0	1.0	8.0	ns	Figure 8, Figure 9
	APAR or B _n , BPAR							riguio o
t _S (H)	Setup Time, HIGH or LOW	5.0	1.6		5.0			Figure 12,
t _S (L)	A _n , B _n to LEA, LEB	5.0	1.8		5.0		ns	Figure 13
t _H (H)	Hold Time, HIGH or LOW	0	-1.7		0		ns	Figure 12,
t _H (L)	A _n , B _n to LEA, LEB	0	-1.5		0		115	Figure 13
t _W	Pulse Width for LEA, LEB	6.0	2.0		6.0		ns	Figure 14



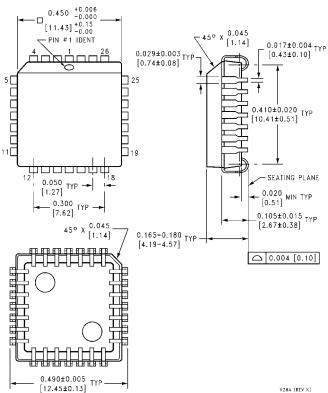








Physical Dimensions inches (millimeters) unless otherwise noted (Continued)



28-Lead Plastic Lead Chip Carrier (PLCC), JEDEC MO-047, 0.450 Square Package Number V28A

Fairchild does not assume any responsibility for use of any circuitry described, no circuit patent licenses are implied and Fairchild reserves the right at any time without notice to change said circuitry and specifications.

LIFE SUPPORT POLICY

FAIRCHILD'S PRODUCTS ARE NOT AUTHORIZED FOR USE AS CRITICAL COMPONENTS IN LIFE SUPPORT DEVICES OR SYSTEMS WITHOUT THE EXPRESS WRITTEN APPROVAL OF THE PRESIDENT OF FAIRCHILD SEMICONDUCTOR CORPORATION. As used herein:

- Life support devices or systems are devices or systems which, (a) are intended for surgical implant into the body, or (b) support or sustain life, and (c) whose failure to perform when properly used in accordance with instructions for use provided in the labeling, can be reasonably expected to result in a significant injury to the user.
- A critical component in any component of a life support device or system whose failure to perform can be reasonably expected to cause the failure of the life support device or system, or to affect its safety or effectiveness.

www.fairchildsemi.com